



Description

BSD5C051V is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The BSD5C051V has an ultra-low capacitance with a typical value at 0.3pF, and complies with the IEC 61000-4-2 (ESD) with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a SOD-523 lead-free package. The small size, ultra-low capacitance and high ESD surge protection make BSD5C051V an ideal choice to protect cell phone, digital visual interfaces and other high speed ports.

Features

- Ultra low capacitance: 0.3pF typical
- Ultra low leakage: nA level
- Operating voltage: 5V
- Low clamping voltage
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lightning) 6A (8/20 μs)
- RoHS Compliant

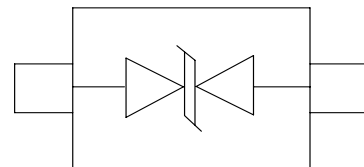
Mechanical Characteristics

- Package: SOD-523
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Visual Interface (DVI)
- PCI Express and Serial SATA Ports

SOD-523



Circuit diagram



55F= Device code

Marking (Top View)

Ordering Information

Part Number	Packaging	Reel Size
BSD5C051V	3000/Tape & Reel	7 inch

Absolute maximum ratings

Parameter	Symbol	Rating	Unit
Peak pulse power ($t_p = 8/20\mu s$)	P_{pk}	60	W
Peak pulse current ($t_p = 8/20\mu s$)	I_{PP}	6	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 30	kV
ESD according to IEC61000-4-2 contact discharge		± 30	
Junction temperature	T_J	125	$^{\circ}C$
Operating temperature	T_{OP}	-40~85	$^{\circ}C$
Lead temperature	T_L	260	$^{\circ}C$
Storage temperature	T_{STG}	-55~150	$^{\circ}C$

Electrical characteristics ($T_A=25^{\circ}C$, unless otherwise noted)

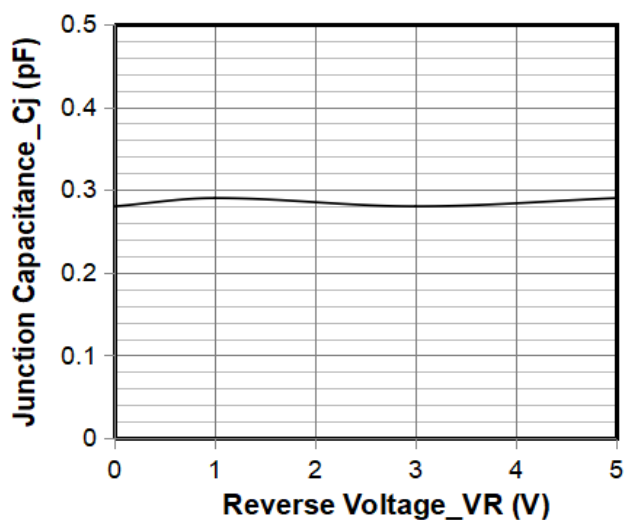
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse maximum working voltage	V_{RWM}				5.0	V
Reverse leakage current	I_R	$V_{RWM} = 5V$		<5	200	nA
Reverse breakdown voltage	V_{BR}	$I_T = 1mA$	5.8		9.5	V
Clamping voltage ¹⁾	V_{CL}	$I_{PP} = 16A, t_p = 100ns$		9		V
Dynamic resistance ¹⁾	R_{DYN}			0.22		Ω
Clamping voltage ²⁾	V_{CL}	$V_{ESD} = 8kV$		9		V
Clamping voltage ³⁾	V_{CL}	$I_{PP} = 1A, t_p = 8/20\mu s$		6	7.5	V
		$I_{PP} = 6A, t_p = 8/20\mu s$		8	10	V
Junction capacitance	C_J	$V_R = 0V, f = 1MHz$		0.30	0.40	pF

Notes:

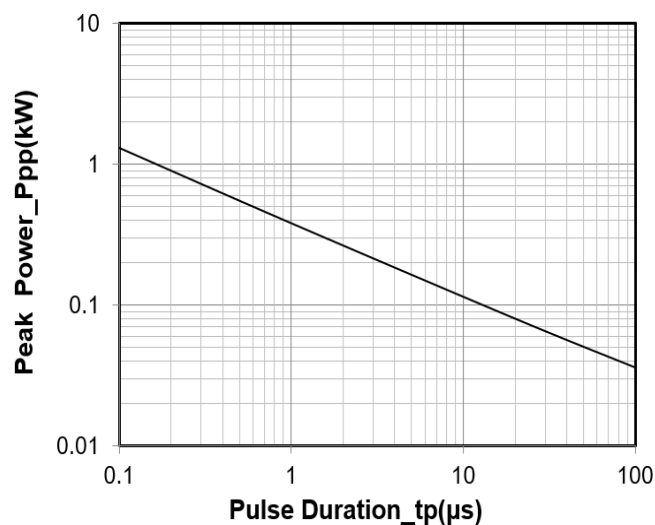
- 1) TLP parameter: $Z_0 = 50\Omega$, $t_p = 100ns$, $t_r = 0.2ns$, averaging window from 70ns to 90ns. R_{DYN} is calculated from 4A to 16A.
- 2) Contact discharge mode, according to IEC61000-4-2.
- 3) Non-repetitive current pulse, according to IEC61000-4-5.

Typical Performance Characteristics (TA=25°C unless otherwise Specified)

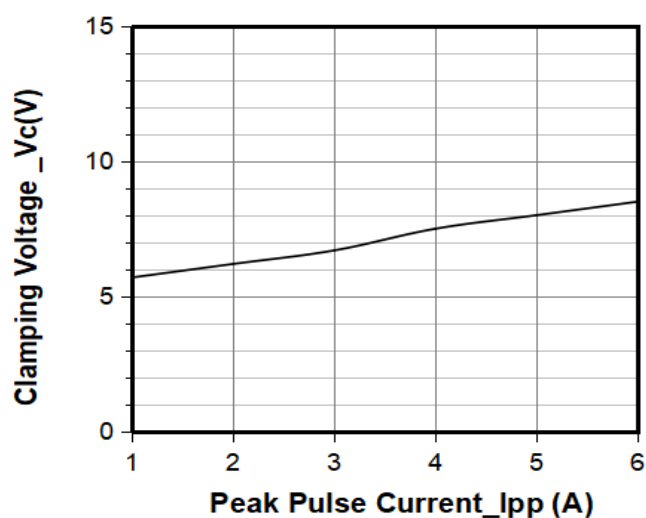
BSD5C051V



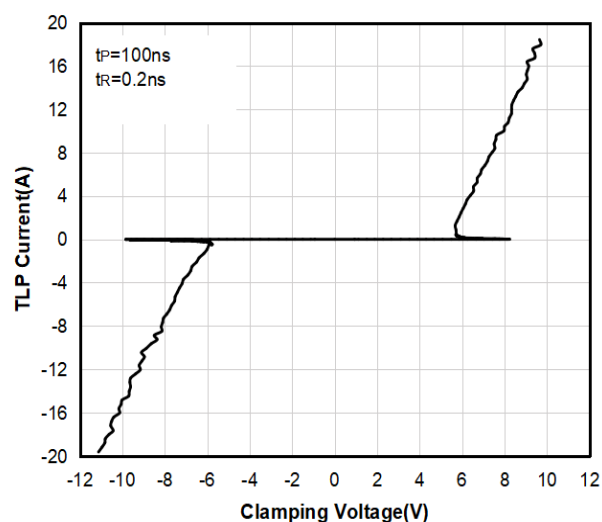
Junction Capacitance vs. Reverse Voltage



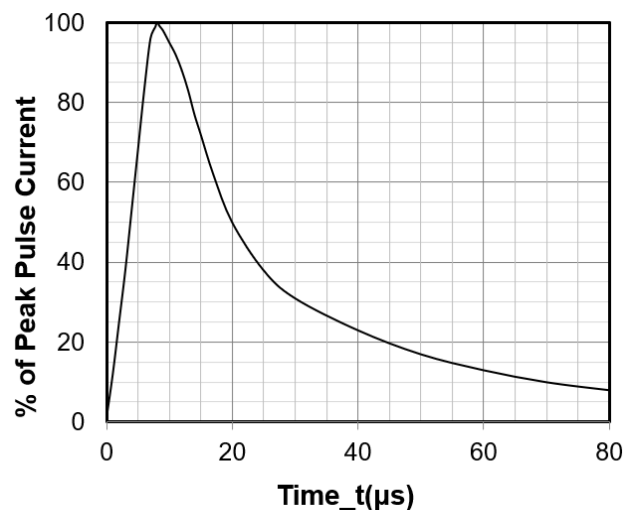
Peak Pulse Power vs. Pulse Time



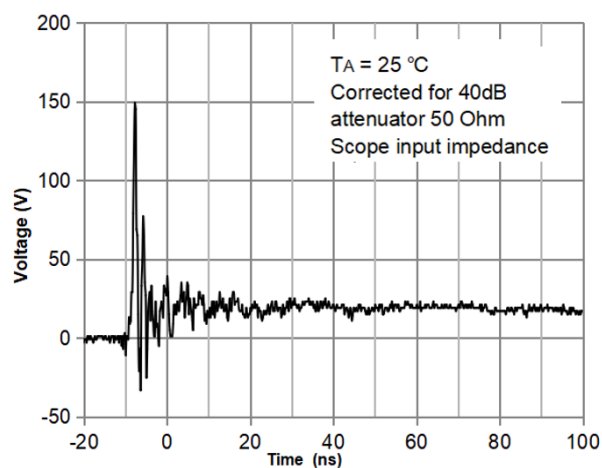
Clamping Voltage vs. Peak Pulse Current ($t_p = 8/20 \mu s$)



TLP Measurement



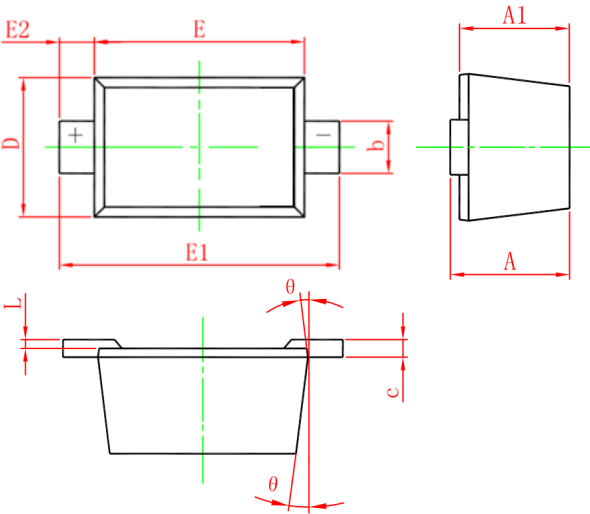
8 X 20 μs Pulse Waveform



ESD Clamping Voltage

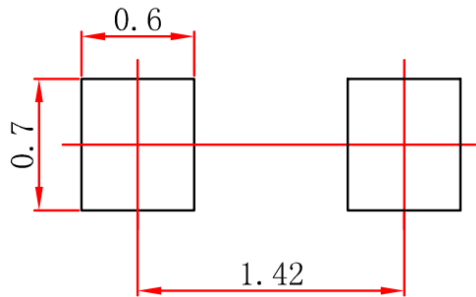
8 kV Contact per IEC61000-4-2

SOD-523 Package Outline Drawing



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.51	--	0.77	0.020	--	0.031
A1	0.50	--	0.70	0.020	--	0.028
b	0.25	--	0.35	0.010	--	0.014
c	0.08	--	0.15	0.003	--	0.006
D	0.75	--	0.85	0.030	--	0.033
E	1.10	--	1.30	0.043	--	0.051
E1	1.50	--	1.70	0.059		0.067
E2	0.20REF			0.008REF		
L	0.01	--	0.07	0.001	--	0.003
Θ	7° REF			7° REF		

Suggested Land Pattern



Unit: mm